these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.--

In the Claims:

Please cancel claims 36 and 81.

Please amend claims 37, 38, 39, 82, 84, and 85 as follows:

37. (Amended) A method of forming a semiconductor device, comprising:

depositing a first conductive layer having a surface and having an ability to associate with oxygen;

incorporating an oxygen-free material directly into said surface to passivate the surface of said first conductive layer to reduce the ability of the first conductive layer to associate with oxygen;

depositing a second conductive layer on said surface after incorporating the oxygen-free material into the surface;

exposing said second conductive layer to a thermal process;

and wherein said step of depositing a first conductive layer comprises depositing a capacitor plate;

and wherein said method further comprises depositing an insulator over said second conductive layer; and

said step of exposing said second conductive layer to a thermal process comprises flowing said insulator.

38. (Amended) The method in claim 37, wherein:

said step of depositing a first conductive layer comprises depositing a plug; and

said step of exposing said second conductive layer to a thermal process comprises

flowing said second conductive layer.

Cont'd D2

39. (Amended) The method in claim 37, wherein said step of exposing said second conductive layer to a thermal process comprises exposing said second conductive layer to an alloy process.

Amend E2

82. (Amended) A method of forming a semiconductor device, comprising

providing a first conductive layer having a surface and having an ability to associate with oxygen;

placing the surface of the first conductive layer in direct contact with an oxygen-free atmosphere under appropriate conditions to passivate the surface and reduce the ability of the first conductive layer to associate with oxygen;

D3

providing a second conductive layer on the surface of the first conductive layer;

subjecting the second conductive layer to a thermal process; and wherein depositing a first conductive layer forms a capacitor plate and wherein the process further comprises depositing an insulator over the second conductive layer and wherein exposing the second conductive layer to a thermal process comprises flowing the insulator.

Sub F' D4

84. (Amended) The method in claim 82 further comprising depositing a plug on which the first conductive layer is thereafter deposited, and wherein exposing the second conductive layer to a thermal process comprises flowing the second conductive layer.

85. (Amended) The method in claim 82, wherein exposing the conductive layer to a thermal process comprises exposing the conductive layer to an alloy process.